



STS1NK60Z

N-CHANNEL 600V - 13Ω - 0.25A - SO-8
Zener-Protected SuperMESH™ Power MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D	P _w
STS1NK60Z	600 V	< 15 Ω	0.25 A	2 W

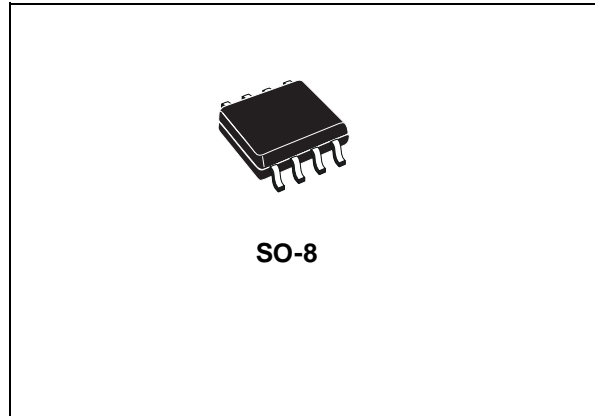
- TYPICAL R_{DS(on)} = 13Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- ESD IMPROVED CAPABILITY
- 100% AVALANCHE TESTED
- NEW HIGH VOLTAGE BENCHMARK
- GATE CHARGE MINIMIZED

DESCRIPTION

The SuperMESH™ series is obtained through an extreme optimization of ST's well established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly down, special care is taken to ensure a very good dv/dt capability for the most demanding applications. Such series complements ST full range of high voltage MOSFETs including revolutionary MDmesh™ products.

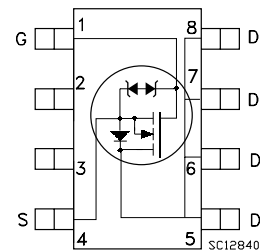
APPLICATIONS

- AC ADAPTORS AND BATTERY CHARGERS
- SWITCH MODE POWER SUPPLIES (SMPS)



SO-8

INTERNAL SCHEMATIC DIAGRAM



ORDERING INFORMATION

SALES TYPE	MARKING	PACKAGE	PACKAGING
STS1NK60Z	S1NK60Z	SO-8	TAPE & REEL

STS1NK60Z

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	600	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 kΩ)	600	V
V _{GS}	Gate- source Voltage	± 30	V
I _D	Drain Current (continuous) at T _C = 25°C	0.25	A
I _D	Drain Current (continuous) at T _C = 100°C	0.16	A
I _{DM} (•)	Drain Current (pulsed)	1	A
P _{TOT}	Total Dissipation at T _C = 25°C	2	W
	Derating Factor	0.016	W/°C
V _{ESD(G-S)}	Gate source ESD(HBM-C=100pF, R=1.5KΩ)	800	V
dv/dt (1)	Peak Diode Recovery voltage slope	4.5	V/ns
T _j	Operating Junction Temperature	-55 to 150	°C
T _{stg}	Storage Temperature	-55 to 150	°C

(•) Pulse width limited by safe operating area

(1) I_{SD} ≤ 0.3A, di/dt ≤ 200A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}.

THERMAL DATA

R _{thj-amb}	Thermal Resistance Junction-ambient Max	62.5	°C/W
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GATE-SOURCE ZENER DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV _{GSO}	Gate-Source Breakdown Voltage	I _{GS} =± 1mA (Open Drain)	30			V

PROTECTION FEATURES OF GATE-TO-SOURCE ZENER DIODES

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

ELECTRICAL CHARACTERISTICS ($T_{CASE} = 25^{\circ}C$ UNLESS OTHERWISE SPECIFIED)
 ON/OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 1 \text{ mA}, V_{GS} = 0$	600			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating}, T_C = 125^{\circ}C$			1 50	μA μA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 20V$			± 10	μA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 50 \mu A$	3	3.75	4.5	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10V, I_D = 0.4 \text{ A}$		13	15	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs} (1)$	Forward Transconductance	$V_{DS} = V, I_D = 0.4 \text{ A}$		0.5		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25V, f = 1 \text{ MHz}, V_{GS} = 0$		94 17.6 2.8		pF pF pF
$C_{oss \text{ eq.}} (3)$	Equivalent Output Capacitance	$V_{GS} = 0V, V_{DS} = 0V \text{ to } 480V$		11		pF

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	$V_{DD} = 300V, I_D = 0.4 \text{ A}$ $R_G = 4.7\Omega, V_{GS} = 10 \text{ V}$ (Resistive Load see, Figure 3)		5.5 5		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 480V, I_D = 0.8 \text{ A},$ $V_{GS} = 10V$		4.9 1 2.7	6.9	nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	$V_{DD} = 300V, I_D = 0.4A$ $R_G = 4.7\Omega, V_{GS} = 10 \text{ V}$ (Resistive Load see, Figure 3)		13 28		ns ns
$t_r(V_{off})$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	$V_{DD} = 480V, I_D = 0.8A,$ $R_G = 4.7\Omega, V_{GS} = 10V$ (Inductive Load see, Figure 5)		28 12.5 48		ns ns ns

SOURCE DRAIN DIODE

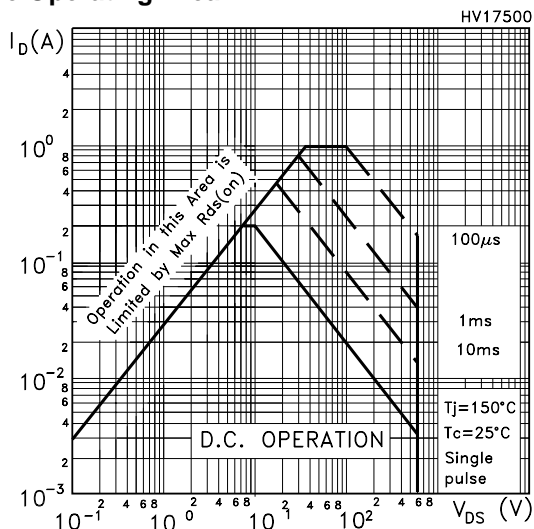
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM} (2)$	Source-drain Current Source-drain Current (pulsed)				0.25 1	A A
$V_{SD} (1)$	Forward On Voltage	$I_{SD} = 0.25A, V_{GS} = 0$			1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 0.8 \text{ A}, di/dt = 100A/\mu s$ $V_{DD} = 20V, T_j = 150^{\circ}C$ (see test circuit, Figure 5)		140 224 3.2		ns nC A

 Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

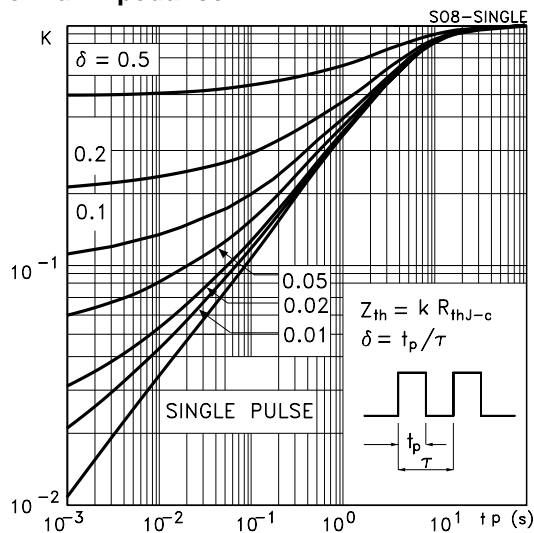
2. Pulse width limited by safe operating area.

 3. $C_{oss \text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .

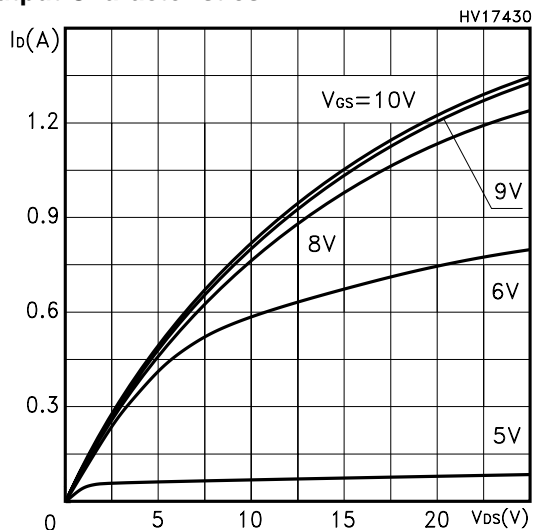
Safe Operating Area



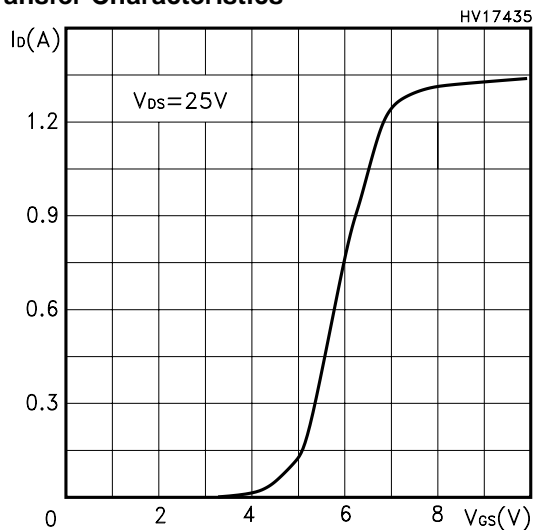
Thermal Impedance



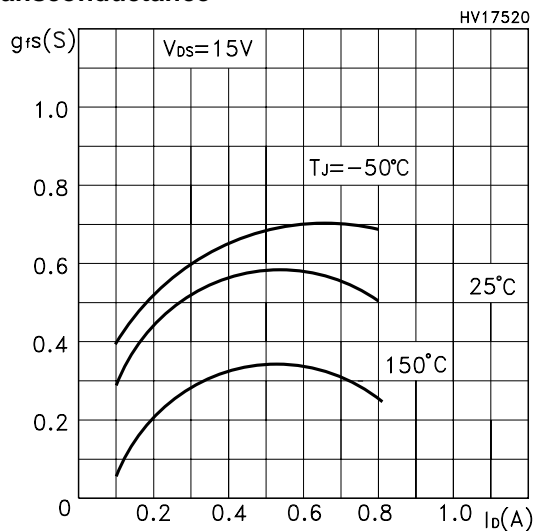
Output Characteristics



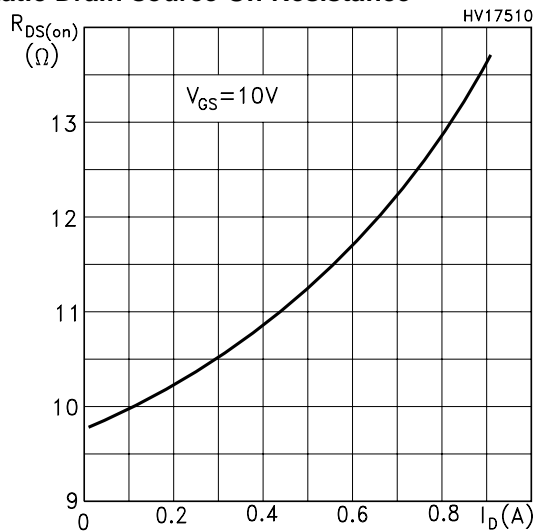
Transfer Characteristics



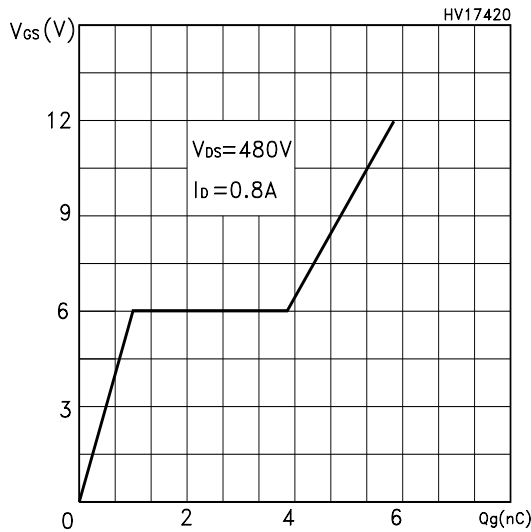
Transconductance



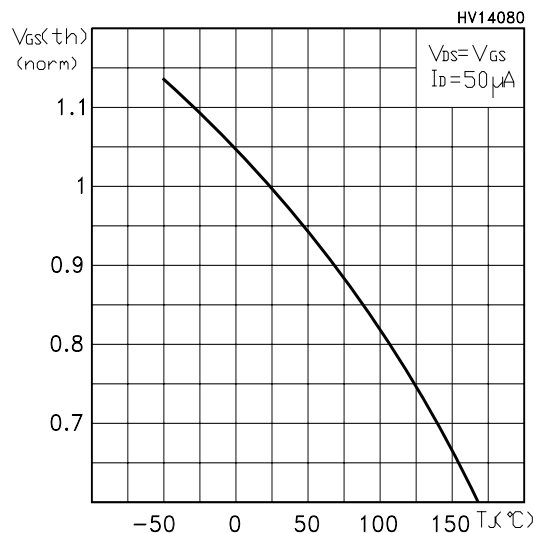
Static Drain-source On Resistance



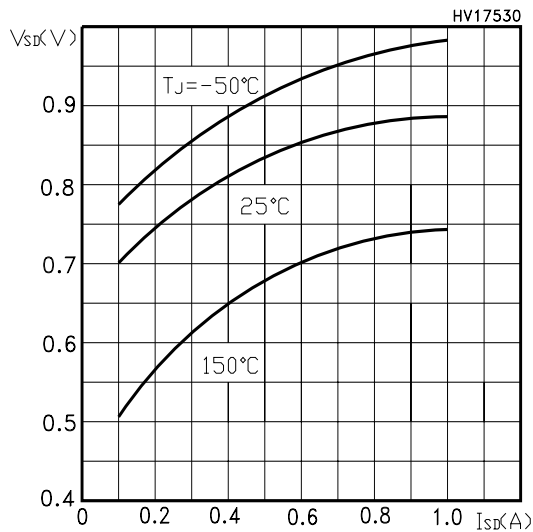
Gate Charge vs Gate-source Voltage



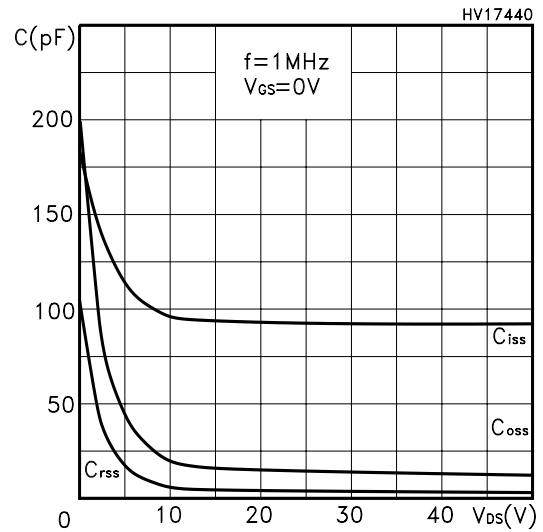
Normalized Gate Threshold Voltage vs Temp.



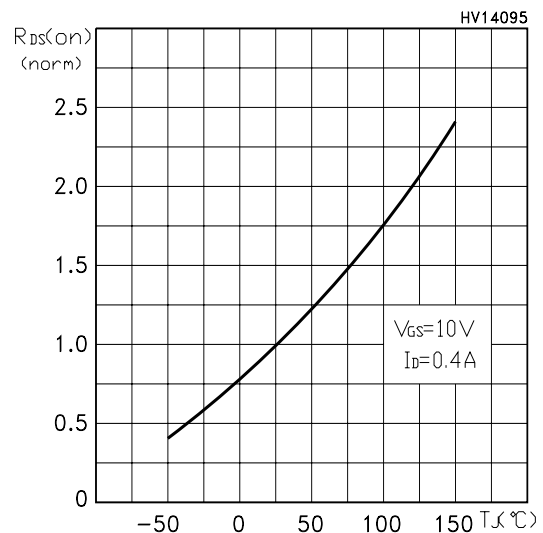
Source-drain Diode Forward Characteristics



Capacitance Variations



Normalized On Resistance vs Temperature



Normalized BVDSS vs Temperature

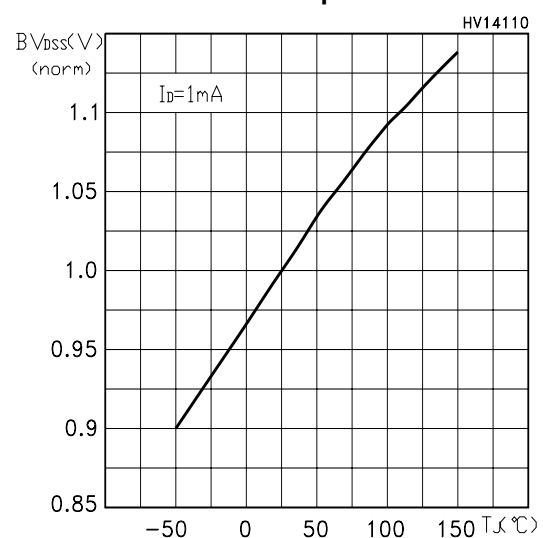


Fig. 1: Unclamped Inductive Load Test Circuit

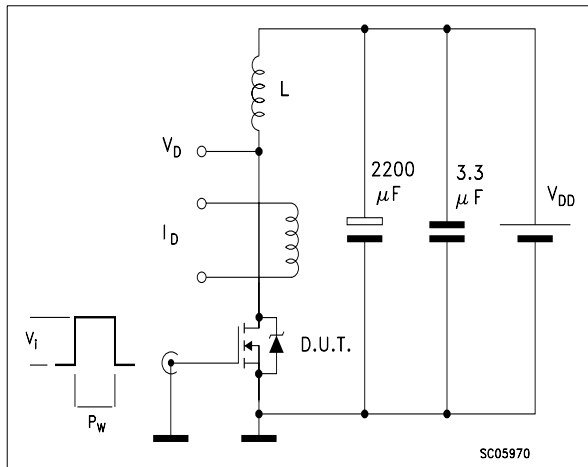


Fig. 2: Unclamped Inductive Waveform

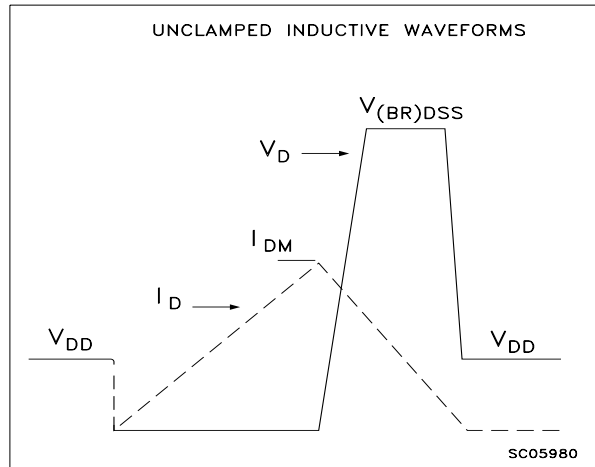


Fig. 3: Switching Times Test Circuit For Resistive Load

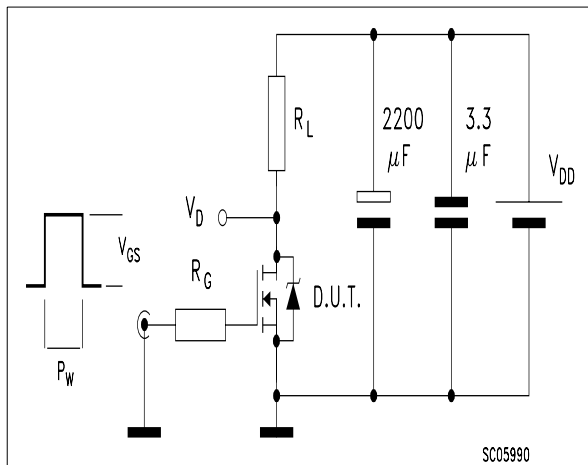


Fig. 4: Gate Charge test Circuit

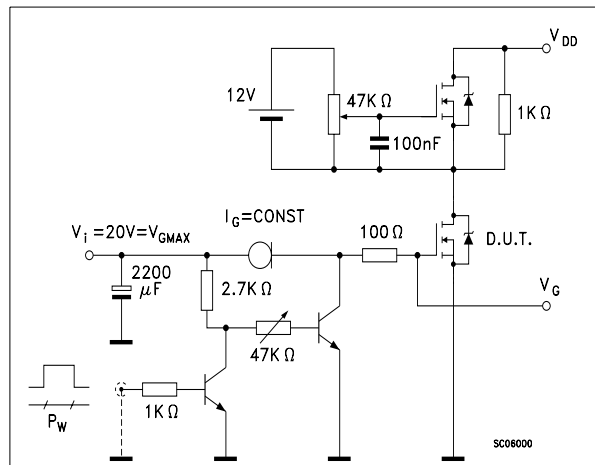
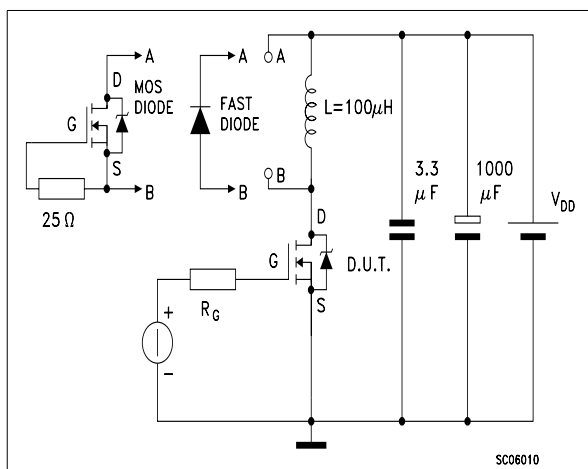
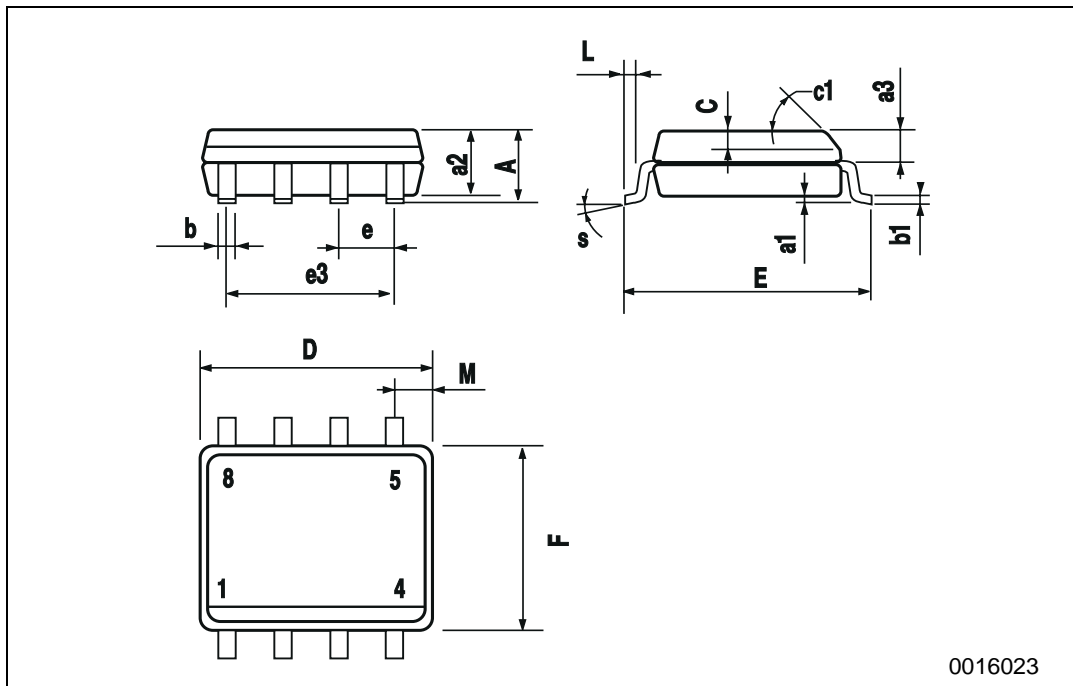


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



SO-8 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.25	0.003		0.009
a2			1.65			0.064
a3	0.65		0.85	0.025		0.033
b	0.35		0.48	0.013		0.018
b1	0.19		0.25	0.007		0.010
C	0.25		0.5	0.010		0.019
c1	45 (typ.)					
D	4.8		5.0	0.188		0.196
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		3.81			0.150	
F	3.8		4.0	0.14		0.157
L	0.4		1.27	0.015		0.050
M			0.6			0.023
S	8 (max.)					



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